

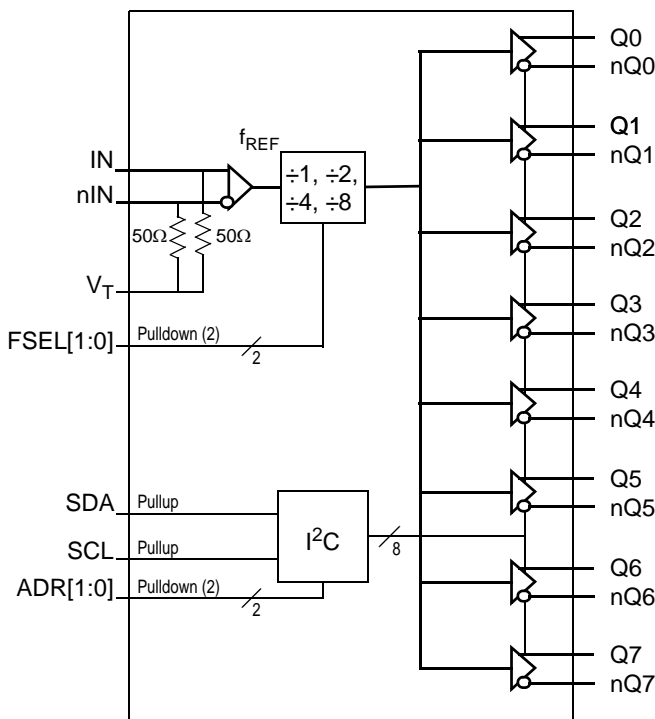
General Description

The 8T74S208C-01 is a high-performance differential LVDS clock divider and fanout buffer. The device is designed for the frequency division and signal fanout of high-frequency, low phase-noise clocks. The 8T74S208C-01 is characterized to operate from a 2.5V power supply. Guaranteed output-to-output and part-to-part skew characteristics make the 8T74S208C-01 ideal for those clock distribution applications demanding well-defined performance and repeatability. The integrated input termination resistors make interfacing to the reference source easy and reduce passive component count. Each output can be individually enabled or disabled in the high-impedance state controlled by a I²C register. On power-up, all outputs are disabled.

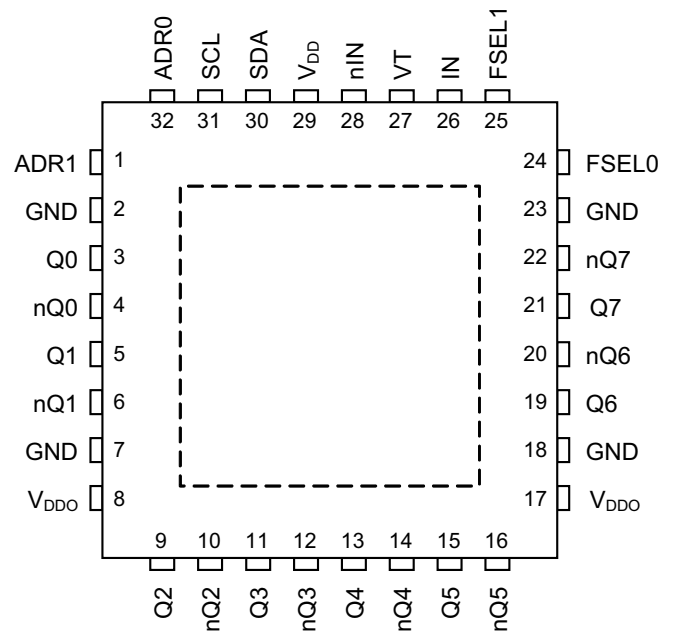
Features

- One differential input reference clock
- Differential pair can accept the following differential input levels: LVDS, LVPECL, CML
- Integrated input termination resistors
- Eight LVDS outputs
- Selectable clock frequency division of ÷1, ÷2, ÷4 and ÷8
- Maximum input clock frequency: 1GHz
- LVC MOS interface levels for the control inputs
- Individual output enabled/ disabled by I²C interface
- Output skew: 45ps (maximum)
- Output rise/fall times: 370ps (maximum)
- Low additive phase jitter, RMS: 96fs (typical)
- Full 2.5V supply voltage
- Outputs disabled at power-up
- Lead-free (RoHS 6) 32-Lead VFQFN packaging
- 40°C to 85°C ambient operating temperature

Block Diagram



Pin Assignment



8T74S208C-01

32-Lead VFQFN, 5mm x 5mm x 0.925mm

Pin Descriptions and Pin Characteristics

Table 1. Pin Descriptions¹

| Number | Name | Type | | Description |
|--------|------------------|-------------------|----------|---|
| 1 | ADR1 | Input | Pulldown | I ² C Address input. LVCMOS/LVTTL interface levels. |
| 2 | GND | Power | | Ground pin. |
| 3 | Q0 | Output | | Differential output pair 0. LVDS interface levels. |
| 4 | nQ0 | Output | | |
| 5 | Q1 | Output | | Differential output pair 1. LVDS interface levels. |
| 6 | nQ1 | Output | | |
| 7 | GND | Power | | Ground pin. |
| 8 | V _{DDO} | Power | | Output supply pin. |
| 9 | Q2 | Output | | Differential output pair 2. LVDS interface levels. |
| 10 | nQ2 | Output | | |
| 11 | Q3 | Output | | Differential output pair 3. LVDS interface levels. |
| 12 | nQ3 | Output | | |
| 13 | Q4 | Output | | Differential output pair 4. LVDS interface levels. |
| 14 | nQ4 | Output | | |
| 15 | Q5 | Output | | Differential output pair 5. LVDS interface levels. |
| 16 | nQ5 | Output | | |
| 17 | V _{DDO} | Power | | Output supply pin. |
| 18 | GND | Power | | Ground pin. |
| 19 | Q6 | Output | | Differential output pair 6. LVDS interface levels. |
| 20 | nQ6 | Output | | |
| 21 | Q7 | Output | | Differential output pair 7. LVDS interface levels. |
| 22 | nQ7 | Output | | |
| 23 | GND | Power | | Ground pin. |
| 24 | FSEL0 | Input | Pulldown | Frequency divider select control. See Table 3A for function. LVCMOS/LVTTL interface levels. |
| 25 | FSEL1 | Input | Pulldown | Frequency divider select control. See Table 3A for function. LVCMOS/LVTTL interface levels. |
| 26 | IN | Input | | Non-inverting differential clock input. RT = 50Ω termination to V _T . |
| 27 | V _T | Termination Input | | Input for termination. Both IN and nIN inputs are internally terminated 50Ω to this pin. See input termination information in the applications section. |
| 28 | nIN | Input | | Inverting differential clock input. RT = 50Ω termination to V _T . |
| 29 | V _{DD} | Power | | Power supply pin. |
| 30 | SDA | I/O | Pullup | I ² C Data Input/Output. Input: LVCMOS/LVTTL interface levels. Output: open drain. |
| 31 | SCL | Input | Pullup | I ² C Clock Input. LVCMOS/LVTTL interface levels. |
| 32 | ADR0 | Input | Pulldown | I ² C Address input. LVCMOS/LVTTL interface levels. |

NOTE 1: *Pulldown* and *Pullup* refer to internal input resistors. See [Table 2, Pin Characteristics](#), for typical values.

Table 2. Pin Characteristics

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------------|-------------------------|-----------------|---------|---------|---------|-----------|
| C_{IN} | Input Capacitance | | | 2 | | pF |
| $R_{PULLDOWN}$ | Input Pulldown Resistor | | | 51 | | $k\Omega$ |
| R_{PULLUP} | Input Pullup Resistor | | | 51 | | $k\Omega$ |

Function Tables

Input Frequency Divider Operation

The FSEL1 and FSEL0 control pins configure the input frequency divider. In the default state (FSEL[1:0] are set to logic 0:0 or left open) the output frequency is equal to the input frequency (divide-by-1). The other FSEL[1:0] settings configure the input divider to divide-by-2, 4 or 8, respectively.

Table 3A. FSEL[1:0] Input Selection Function Table¹

| Input | | Operation |
|-------------|-------------|-------------------------------|
| FSEL1 | FSEL0 | |
| 0 (default) | 0 (default) | $f_{Q[7:0]} = f_{REF} \div 1$ |
| 0 | 1 | $f_{Q[7:0]} = f_{REF} \div 2$ |
| 1 | 0 | $f_{Q[7:0]} = f_{REF} \div 4$ |
| 1 | 1 | $f_{Q[7:0]} = f_{REF} \div 8$ |

NOTE 1: FSEL1, FSEL0 are asynchronous controls

Output Enable Operation

The output enable/disable state of each individual differential output Qx, nQx can be set by the content of the I²C register (see [Table 3C](#)). A logic zero to an I²C bit in register 0 enables the corresponding differential output, while a logic one disables the differential output (see [Table 3B](#)). After each power cycle, the device resets all I²C bits (Dn) to its default state (logic 1) and all Qx, nQx outputs are disabled. After the first valid I²C write, the output enable state is controlled by the I²C register. Setting and changing the output enable state through the I²C interface is asynchronous to the input reference clock.

Table 3B. Individual Output Enable Control

| Bit | Operation |
|-------------|---|
| Dn | |
| 0 | Output Qx, nQx is enabled. |
| 1 (default) | Output Qx, nQx is disabled in high-impedance state. |

Table 3C. Individual Output Enable Control

| Bit | D7 | D6 | D5 | D4 | D3 | D2 | D1 | D0 |
|---------|----|----|----|----|----|----|----|----|
| Output | Q7 | Q6 | Q5 | Q4 | Q3 | Q2 | Q1 | Q0 |
| Default | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 1 |

I²C Interface Protocol

The 8T74S208C-01 uses an I²C slave interface for writing and reading the device configuration to and from the on-chip configuration registers. This device uses the standard I²C write format for a write transaction, and a standard I²C read format for a read transaction. [Figure 1](#) defines the I²C elements of the standard I²C transaction. These elements consist of a start bit, data bytes, an acknowledge or Not-Acknowledge bit and the stop bit. These elements are arranged to make up the complete I²C transactions as shown in [Figure 2](#) and [Figure 3](#). [Figure 2](#) is a write transaction while [Figure 3](#) is read transaction. The 7-bit I²C slave address of the

8T74S208C-01 is a combination of a 5-bit fixed addresses and two variable bits which are set by the hardware pins ADR[1:0] (binary 11010, ADR1, ADR0). Bit 0 of slave address is used by the bus controller to select either the read or write mode. The hardware pins ADR1 and ADR0 and should be individually set by the user to avoid address conflicts of multiple 8T74S208C-01 devices on the same bus.

Table 3D. I²C Slave Address

| 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|---|---|---|---|---|------|------|-----|
| 1 | 1 | 0 | 1 | 0 | ADR1 | ADR0 | R/W |

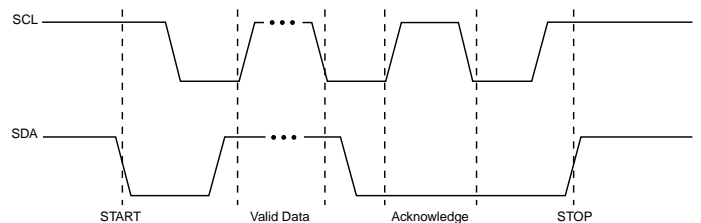


Figure 1. Standard I²C Transaction

START (S) – defined as high-to-low transition on SDA while holding SCL HIGH.

DATA – between START and STOP cycles, SDA is synchronous with SCL. Data may change only when SCL is LOW and must be stable when SCL is HIGH.

ACKNOWLEDGE (A) – SDA is driven LOW before the SCL rising edge and held LOW until the SCL falling edge.

STOP (P) – defined as low-to-high transition on SDA while holding SCL HIGH

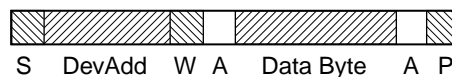


Figure 2. Write Transaction

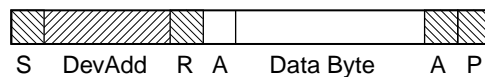


Figure 3. Read Transaction

S – Start or Repeated Start

W – R/W is set for Write

R – R/W is set for Read

A – Ack

DevAdd –7 bit Device Address

P – Stop

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the [DC Electrical Characteristics](#) or [AC Electrical Characteristics](#) is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

| Item | Rating |
|---|--------------------------|
| Supply Voltage, V_{DD} | 4.6V |
| Inputs, V_I | -0.5V to $V_{DD} + 0.5V$ |
| Input Termination Current, I_{VT} | $\pm 35mA$ |
| Outputs, I_O Continuous Current Surge Current | 10mA 15mA |
| Storage Temperature, T_{STG} | -65°C to 150°C |
| Maximum Junction Temperature, T_{JMAX} | 125°C |
| ESD - Human Body Model ¹ | 2000V |
| ESD - Charged Device Model ¹ | 500V |

NOTE 1: According to JEDEC/JS-001-2012/JESD22-C101E.

DC Electrical Characteristics

Table 4A. Power Supply DC Characteristics, $V_{DD} = V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------|-----------------------|--|---------|---------|---------|-------|
| V_{DD} | Power Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| V_{DDO} | Output Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| I_{DD} | Power Supply Current | | | 54 | 64 | mA |
| I_{DDO} | Output Supply Current | All Outputs are Enabled and Terminated | | 155 | 182 | mA |

Table 4B. LVCMOS/LVTTL Input DC Characteristics, $V_{DD} = V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units | |
|----------|---------------------------------|---------------------|--------------------------------|---------|---------|----------------|---------|
| V_{IH} | Input High Voltage ¹ | FSEL[1:0], ADR[1:0] | $V_{DD} = 2.5V \pm 5\%$ | 1.7 | | $V_{DD} + 0.3$ | V |
| | | SCL, SDA | $V_{DD} = 2.5V \pm 5\%$ | 1.9 | | $V_{DD} + 0.3$ | V |
| V_{IL} | Input Low Voltage ¹ | FSEL[1:0], ADR[1:0] | $V_{DD} = 2.5V \pm 5\%$ | -0.3 | | 0.7 | V |
| | | SCL, SDA | $V_{DD} = 2.5V \pm 5\%$ | -0.3 | | 0.5 | V |
| I_{IH} | Input High Current | FSEL[1:0], ADR[1:0] | $V_{DD} = V_{IN} = 2.625V$ | | | 150 | μA |
| | | SCL, SDA | $V_{DD} = V_{IN} = 2.625V$ | | | 5 | μA |
| I_{IL} | Input Low Current | FSEL[1:0], ADR[1:0] | $V_{DD} = 2.625V, V_{IN} = 0V$ | -10 | | | μA |
| | | SCL, SDA | $V_{DD} = 2.625V, V_{IN} = 0V$ | -150 | | | μA |

NOTE 1: V_{IL} should not be lower than -0.3V and V_{IH} should not be higher than $V_{DD} + 0.3V$.

Table 4C. Differential Input DC Characteristics, $V_{DD} = V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------------|---|--------------------------------|---------|---------|-----------------------|----------|
| V_{IN} | Input Voltage Swing ¹ | IN, nIN | 0.15 | | 1.2 | V |
| V_{CMR} | Common Mode Input Voltage ^{1, 2} | | 1.2 | | $V_{DD} - (V_{IN}/2)$ | V |
| V_{DIFF} | Differential Input Voltage Swing | IN, nIN | 0.3 | | 2.4 | V |
| R_{IN} | Input Resistance | IN, nIN to V_T | 40 | 50 | 60 | Ω |
| $R_{IN, DIFF}$ | Differential Input Resistance | IN to nIN, $V_T = \text{open}$ | 80 | 100 | 120 | Ω |

NOTE 1: V_{IL} should not be less than -0.3V and V_{IH} should not be greater than V_{DD} .

NOTE 2: *Common Mode Input Voltage* is defined as the cross point.

Table 4D. LVDS DC Characteristics, $V_{DD} = V_{DDO} = 2.5V$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------|-----------------------------|-----------------|---------|---------|---------|-------|
| V_{OD} | Differential Output Voltage | | 247 | | 454 | mV |
| ΔV_{OD} | V_{OD} Magnitude Change | | | | 50 | mV |
| V_{OS} | Offset Voltage | | 1.120 | | 1.425 | V |
| ΔV_{OS} | V_{OS} Magnitude Change | | | | 50 | mV |

AC Electrical Characteristics

Table 5. AC Electrical Characteristics, $V_{DD} = V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$ ¹

| Symbol | Parameter | | Test Conditions | Minimum | Typical | Maximum | Units |
|--------------|---|--------------------|--|---------|---------|---------|---------|
| f_{REF} | Input Frequency | IN, nIN | | | | 1 | GHz |
| f_{SCL} | I ² C Clock Frequency | | | | | 400 | kHz |
| t_{JIT} | Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section, measured with FSEL[1:0] = 00 | | $f_{REF} = 156.25MHz$, Integration Range: 12kHz – 20MHz | | 96 | 120 | fs |
| t_{PD} | Propagation Delay ² | IN, nIN to Qx, nQx | FSEL[1:0] = 00 | 420 | | 700 | ps |
| | | | FSEL[1:0] = 01 | 580 | | 880 | ps |
| | | | FSEL[1:0] = 10 | 680 | | 1080 | ps |
| | | | FSEL[1:0] = 11 | 780 | | 1180 | ps |
| $t_{sk(o)}$ | Output Skew ^{3, 4} | | | | 45 | ps | |
| $t_{sk(p)}$ | Pulse Skew | | FSEL[1:0] = 00 | | | 55 | ps |
| $t_{sk(pp)}$ | Part-to-Part Skew ^{4, 5, 6} | | | | | 200 | ps |
| odc | Output Duty Cycle ⁷ | | FSEL[1:0] = 00 | | 50 | | % |
| | | | FSEL[1:0] = 01 | 48 | 50 | 52 | % |
| | | | FSEL[1:0] = 10 | 48 | 50 | 52 | % |
| | | | FSEL[1:0] = 11 | 48 | 50 | 52 | % |
| t_{PDZ} | Output Enable and Disable Time ⁸ | | Output Enable/ Disable State from/ to Active/ Inactive | | 1 | | μs |
| t_R / t_F | Output Rise/ Fall Time | | 20% to 80% | | 155 | 230 | ps |
| | | | 10% to 90% | | 245 | 370 | ps |

NOTE 1: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 2: Measured from the differential input crosspoint to the differential output crosspoint.

NOTE 3: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the differential crosspoint.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 5: Defined as skew between outputs on different devices operating at the same supply voltage, same temperature, same frequency and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential crosspoint.

NOTE 6: Part-to-part skew specification does not guarantee divider synchronization among devices.

NOTE 7: If FSEL[1:0] = 00 (divide-by-one), the output duty cycle will depend on the input duty cycle.

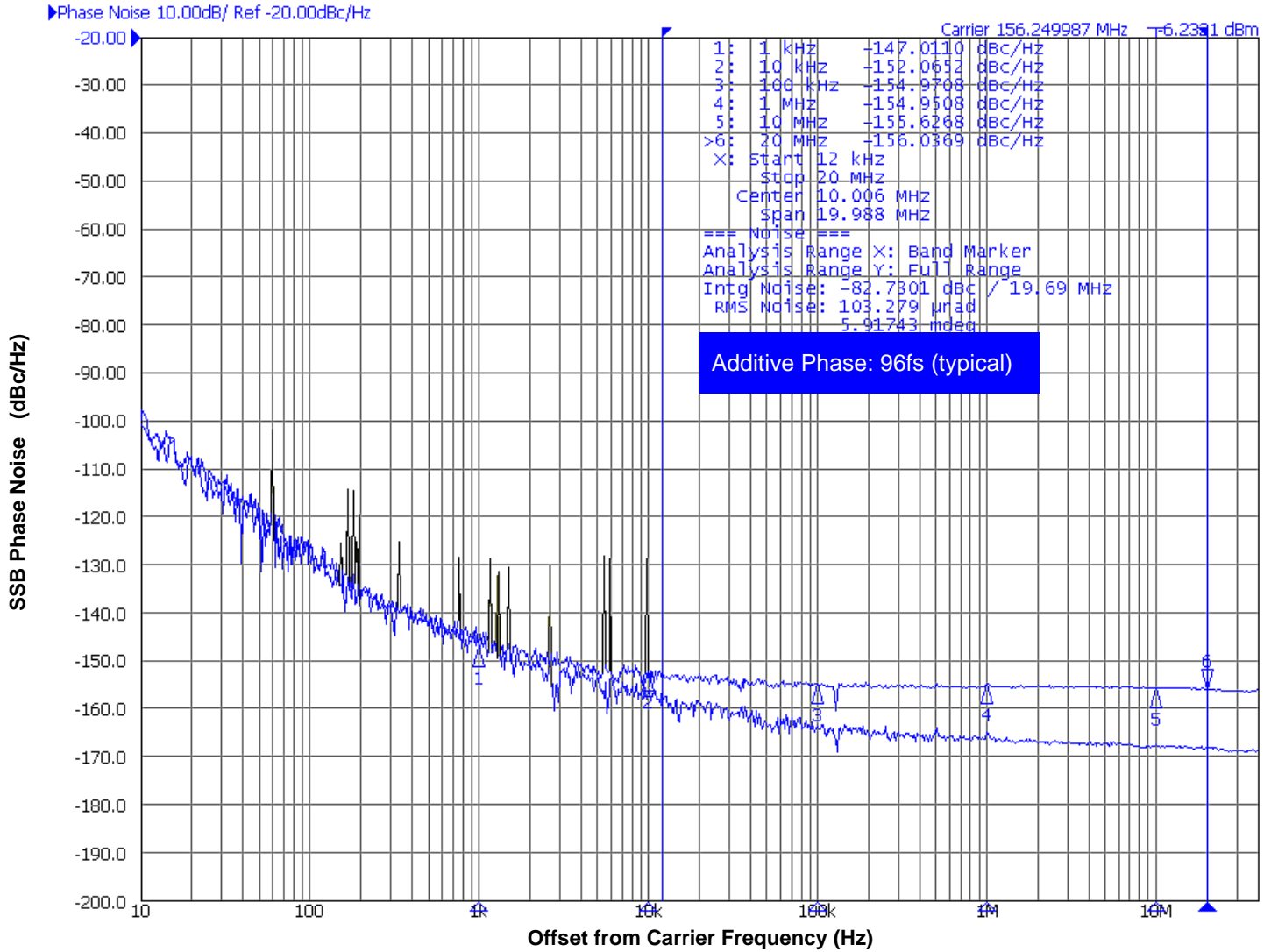
NOTE 8: Measured from SDA rising edge of I²C stop command.

Additive Phase Jitter

The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the **dBc Phase Noise**. This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio

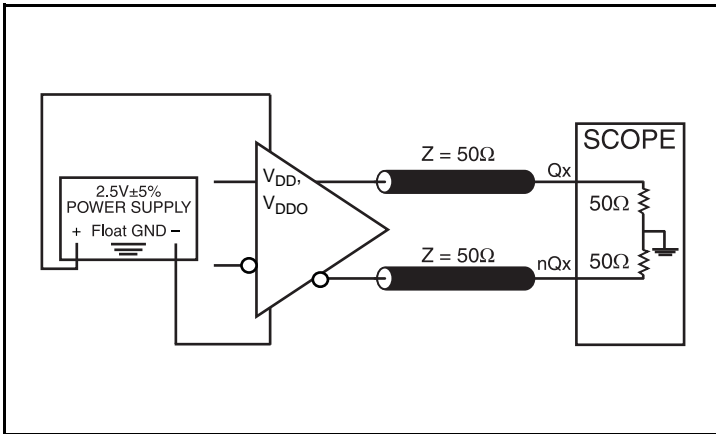
of the power in the 1Hz band to the power in the fundamental. When the required offset is specified, the phase noise is called a **dBc** value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.

Typical Phase Jitter at 156.25MHz

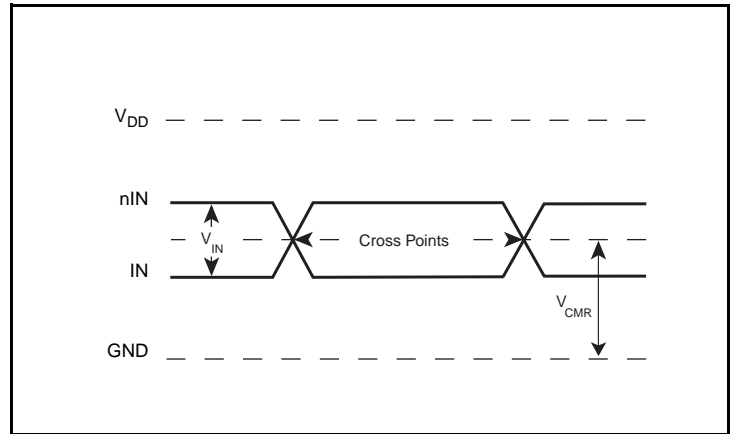


The input source is 156.25MHz Wenzel Oscillator.

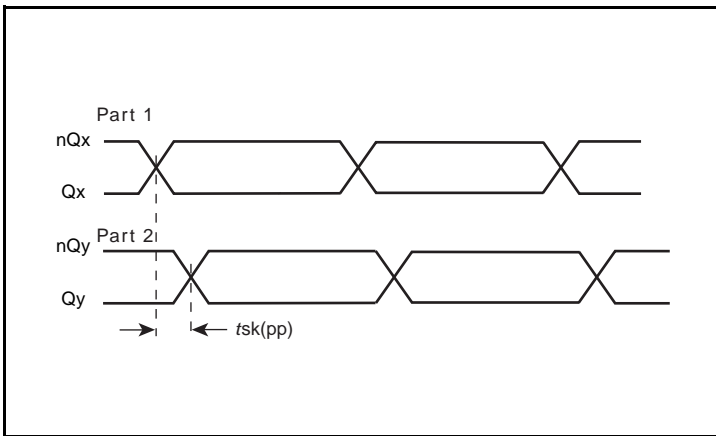
Parameter Measurement Information



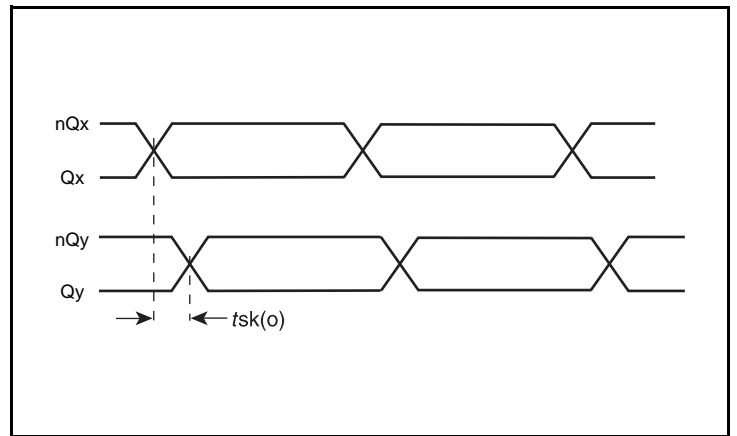
LVDS Output Load AC Test Circuit



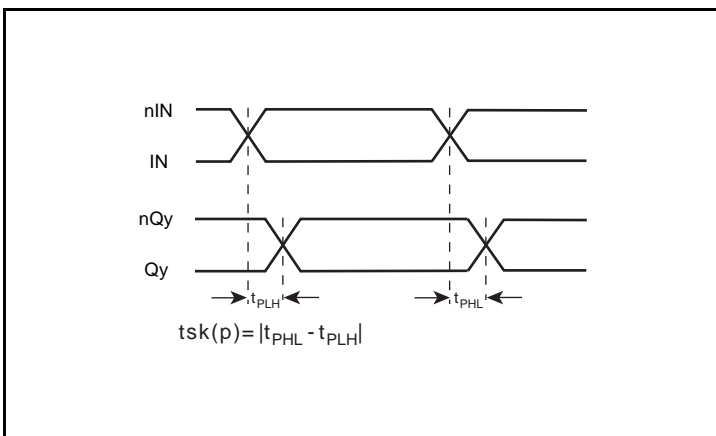
Differential Input Level



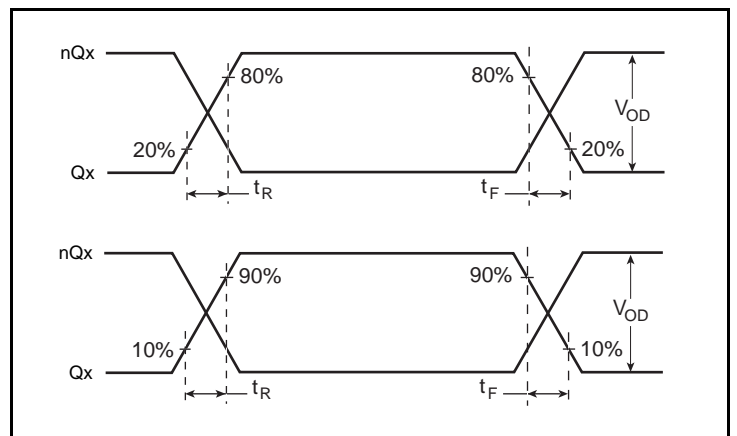
Part-to-Part Skew



Output Skew

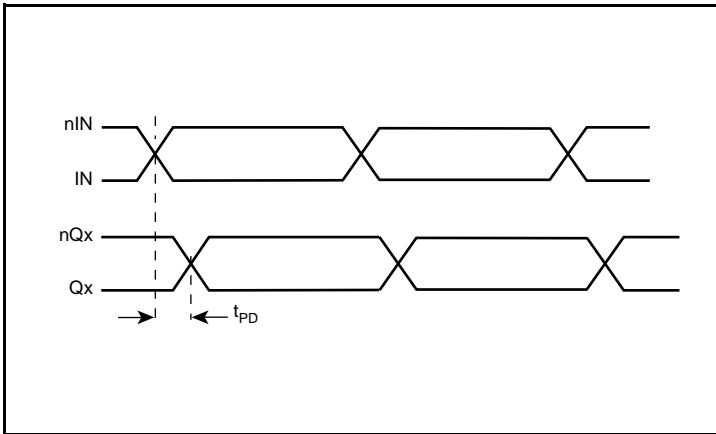


Pulse Skew

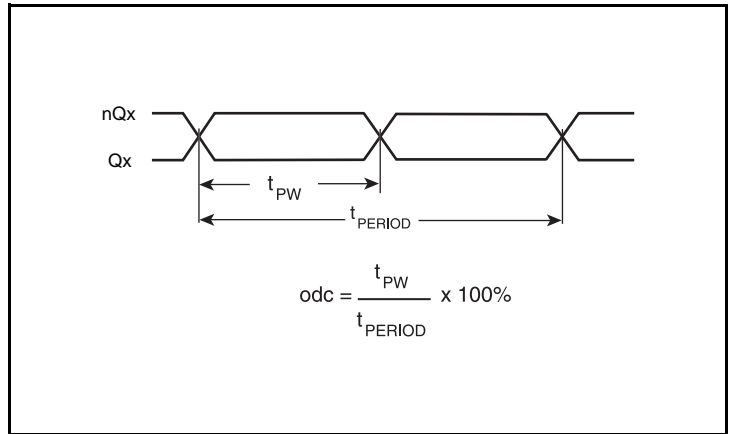


Output Rise/Fall Time

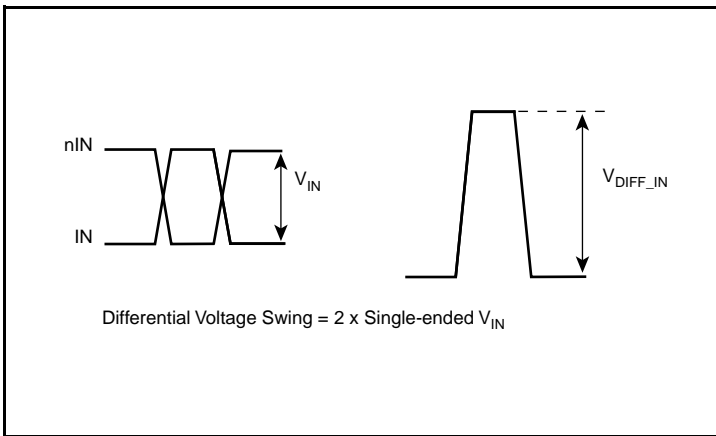
Parameter Measurement Information, continued



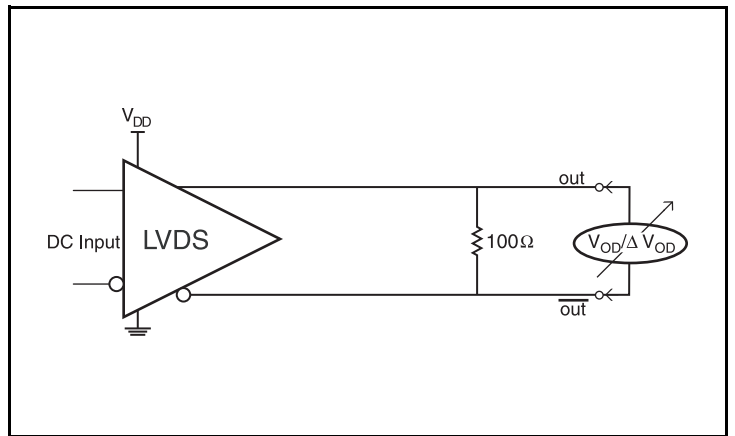
Propagation Delay



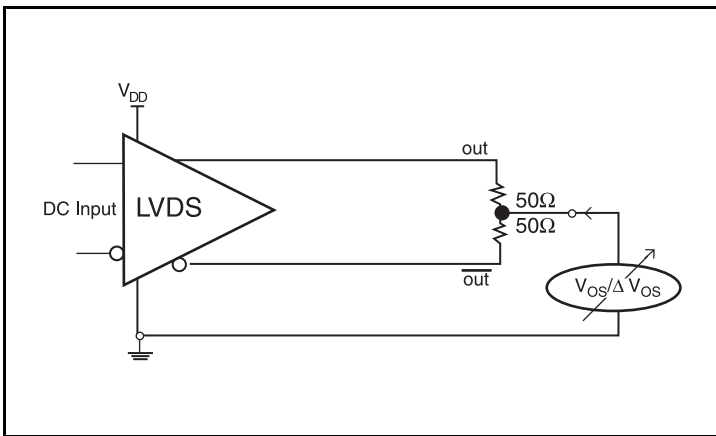
Output Duty Cycle/Pulse Width/Period



Single-Ended & Differential Input Voltage Swing



Differential Output Voltage Setup



Offset Voltage Setup

Applications Information

Differential Input with Built-In 50Ω Termination Interface

The IN/nIN with built-in 50Ω terminations accept LVDS, LVPECL, CML and other differential signals. Both differential signals must meet the V_{IN} and V_{CMR} requirements. [Figure 4A](#) to [Figure 4C](#) show interface examples for the IN/nIN input with built-in 50Ω terminations driven by the most common driver types. The input interfaces

suggested here are examples only. If the driver is from another vendor, use their termination recommendation. Please consult with the vendor of the driver component to confirm the driver termination requirements.

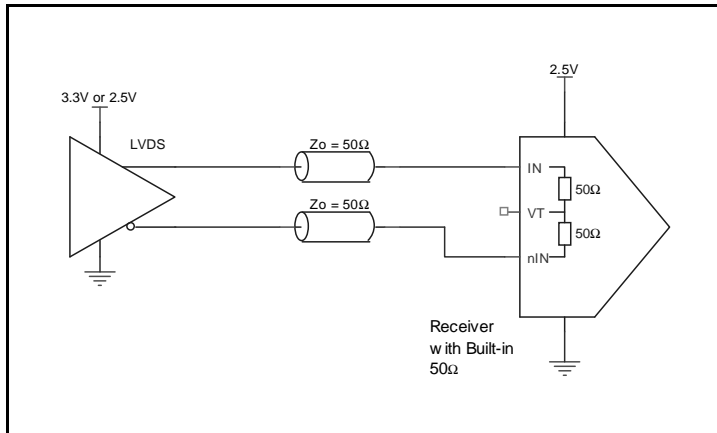


Figure 4A. IN/nIN Input with Built-In 50Ω driven by an LVDS Driver

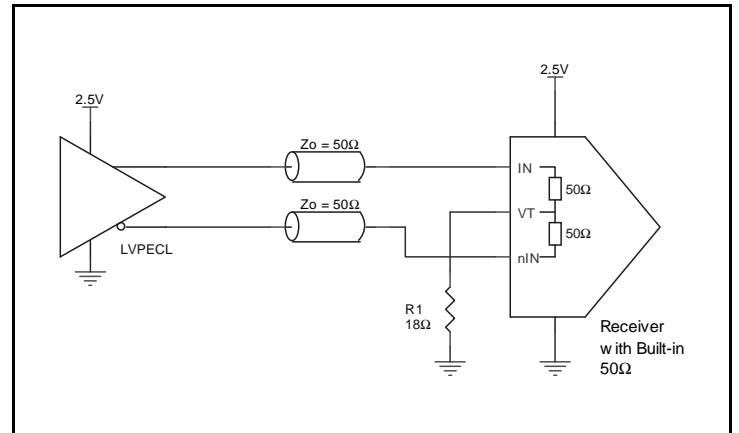


Figure 4C. IN/nIN Input with Built-In 50Ω driven by an LVPECL Driver

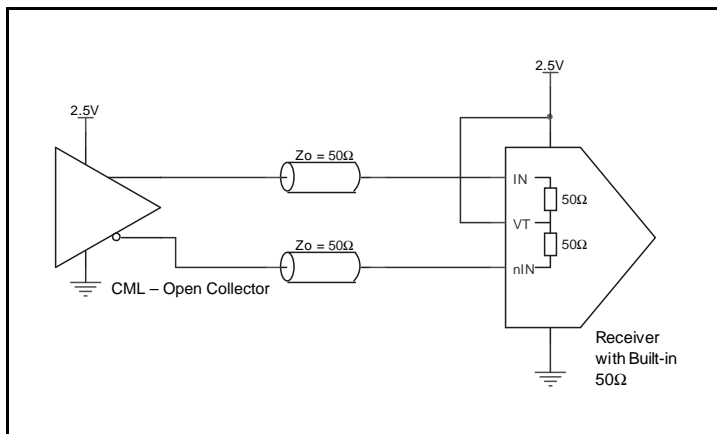


Figure 4B. IN/nIN Input with Built-In 50Ω Driven by a CML Driver with Open Collector

VFQFN EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 5*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as “heat pipes”. The number of vias (i.e. “heat pipes”) are application specific

and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, please refer to the Application Note on the Surface Mount Assembly of Amkor’s Thermally/Electrically Enhance Lead frame Base Package, Amkor Technology.

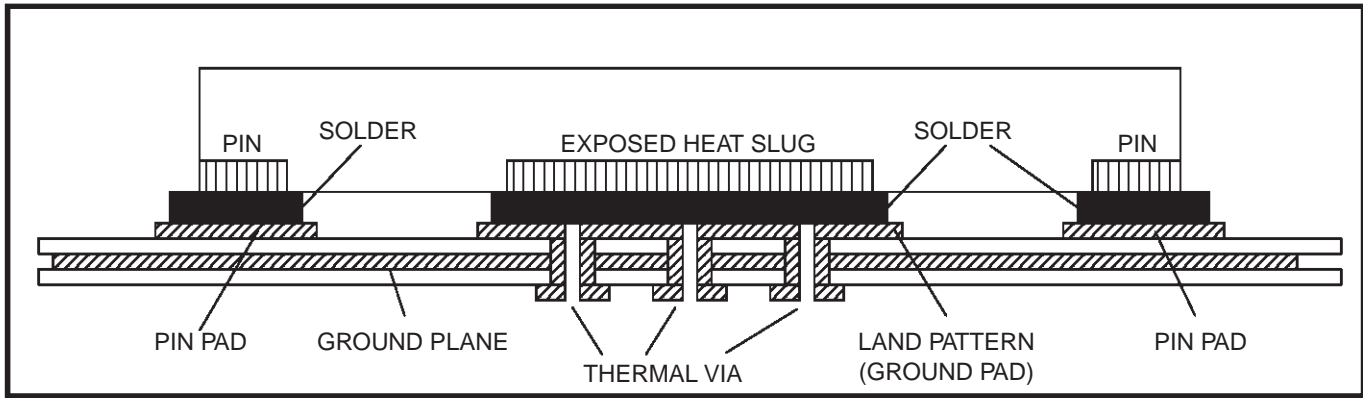


Figure 5. P.C. Assembly for Exposed Pad Thermal Release Path – Side View (drawing not to scale)

Recommendations for Unused Input and Output Pins

Inputs:

LVC MOS Control Pins

All control pins have internal pullup or pulldown resistors; additional resistance is not required but can be added for additional protection. A 1kΩ resistor can be used.

Outputs:

LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100Ω across. If they are left floating, there should be no trace attached.

LVDS Driver Termination

For a general LVDS interface, the recommended value for the termination impedance (Z_T) is between 90Ω and 132Ω . The actual value should be selected to match the differential impedance (Z_0) of your transmission line. A typical point-to-point LVDS design uses a 100Ω parallel resistor at the receiver and a 100Ω differential transmission-line environment. In order to avoid any transmission-line reflection issues, the components should be surface mounted and must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The standard termination schematic as shown in [Figure 6A](#) can be used

with either type of output structure. [Figure 6B](#), which can also be used with both output types, is an optional termination with center tap capacitance to help filter common mode noise. The capacitor value should be approximately 50pF . If using a non-standard termination, it is recommended to contact IDT and confirm if the output structure is current source or voltage source type. In addition, since these outputs are LVDS compatible, the input receiver's amplitude and common-mode input range should be verified for compatibility with the output.

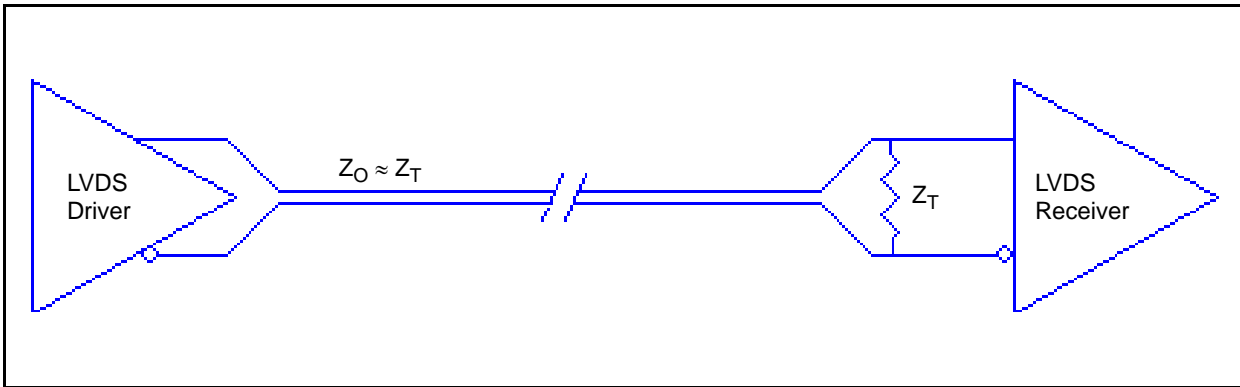


Figure 6A. Standard LVDS Termination

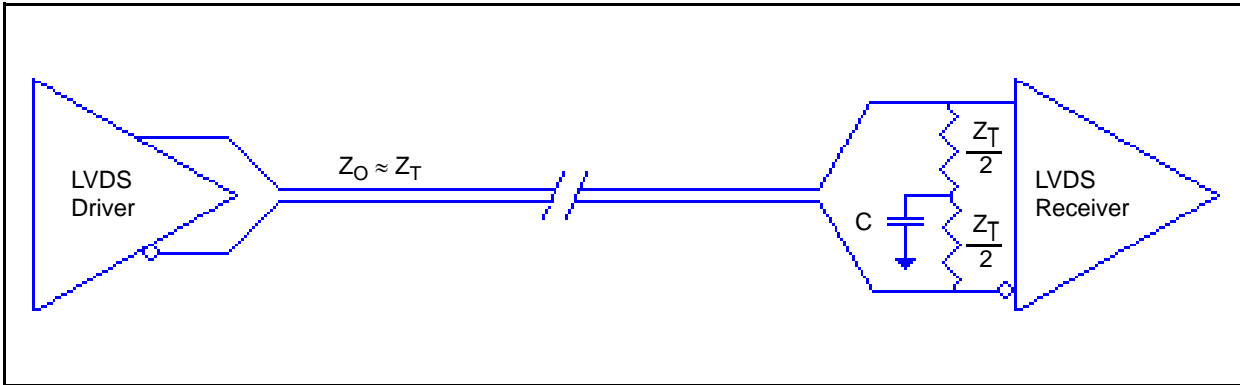


Figure 6B. Optional LVDS Termination

Power Considerations

1. Power Dissipation.

The total power dissipation for the 8T74S208C-01 is the sum of the core power plus the power dissipated due to the load. The following is the power dissipation for $V_{DD} = 2.5V + 5\% = 2.625V$, which gives worst case results.

Note: I_{DD_MAX} and I_{DDO_MAX} @ 85°C = 57.7mA and 164.5mA, respectively.

- Power (core)_{MAX} = $V_{DD_MAX} * I_{DD_MAX} = 2.625V * 57.7mA = 151.46mW$
- Power (output)_{MAX} = $V_{DDO_MAX} * I_{DDO} = 2.625V * 164.5mA = 431.81mW$
- Power Dissipation for internal termination R_T
 Power (R_T)_{MAX} = $(V_{IN_MAX})^2 / 80\Omega = 18mW$

Total Power_{MAX} = (2.625V, with all outputs switching) = 151.46mW + 431.81mW + 18mW = 601.27mW

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_j , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 42.7°C/W per [Table 6](#) below.

Therefore, T_j for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ\text{C} + 0.601\text{W} * 42.7^\circ\text{C}/\text{W} = 111^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 6. Thermal Resistance θ_{JA} for 32-Lead VFQFN, Forced Convection

| θ_{JA} by Velocity | | | |
|---|----------|----------|----------|
| Meters per Second | 0 | 1 | 2.5 |
| Multi-Layer PCB, JEDEC Standard Test Boards | 42.7°C/W | 37.3°C/W | 33.5°C/W |

Reliability Information

Table 7. θ_{JA} vs. Air Flow Table for a 32-Lead VFQFN

| θ_{JA} vs. Air Flow | | | |
|---|----------|----------|------------|
| Meters per Second | 0 | 1 | 2.5 |
| Multi-Layer PCB, JEDEC Standard Test Boards | 42.7°C/W | 37.3°C/W | 33.5°C/W |

Transistor Count

The transistor count for 8T74S208C-01 is 4969.

32-Lead VFQFN Package Outline and Package Dimensions

| REVISIONS | | | |
|-----------|------------------------|--------|----------|
| REV | DESCRIPTION | DATE | APPROVED |
| 00 | INITIAL RELEASE | 2/1/16 | JH |
| 01 | ADD "k" VALUE MIN 0.20 | 2/8/16 | JH |

| SYMBOL | DIMENSION | |
|--------|-----------|-----------|
| | MIN | NOM MAX |
| b | 0.18 | 0.25 0.30 |
| D | 5.00 BSC | |
| E | 5.00 BSC | |
| D2 | 3.00 | 3.15 3.30 |
| E2 | 3.00 | 3.15 3.30 |
| L | 0.30 | 0.40 0.50 |
| e | 0.50 BSC | |
| N | 32 | |
| A | 0.80 | 0.90 1.00 |
| A1 | 0.00 | 0.02 0.05 |
| A3 | 0.2 REF | |
| k | 0.20 | 0.53 REF |

TOP VIEW

SIDE VIEW

BOTTOM VIEW

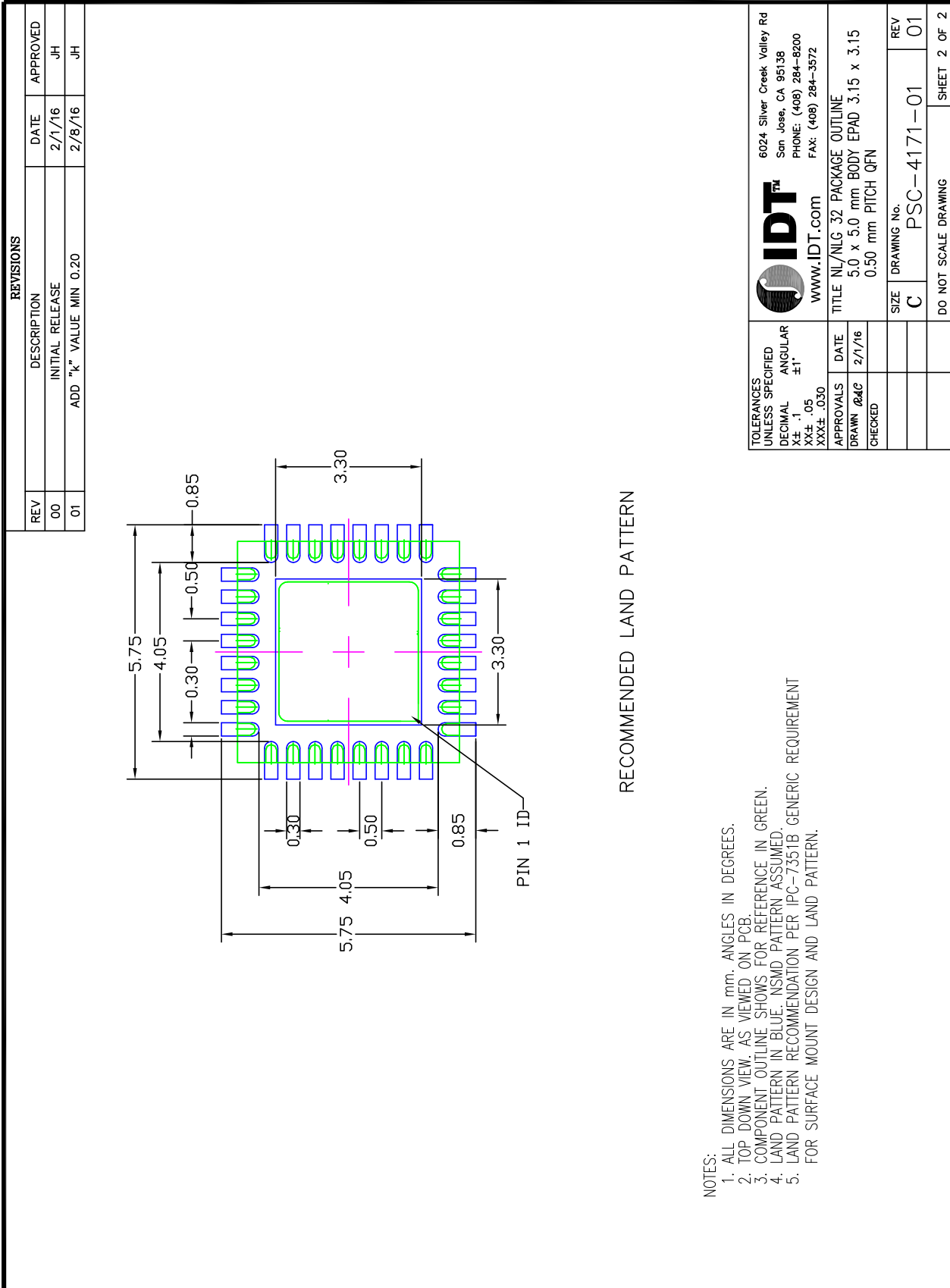
PIN #1 ID OPTION

NOTES:

- ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
- COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
COPLANARITY SHALL NOT EXCEED 0.08 mm.
- WARPAGE SHALL NOT EXCEED 0.10 mm.

| | | |
|---|---|---|
| <p>TOLERANCES UNLESS SPECIFIED</p> <p>DECIMAL ±0.1</p> <p>ANGULAR ±1°</p> <p>XX±.05</p> <p>XXX±.030</p> | <p>6024 Silver Creek Valley Rd San Jose, CA 95136 PHONE: (408) 284-8200 FAX: (408) 284-3572 www.IDT.com</p> | <p>TITLE NL/NLG 32 PACKAGE OUTLINE</p> <p>5.0 x 5.0 mm BODY EPAD 3.15 x 3.15</p> <p>0.50 mm PITCH QFN</p> |
| APPROVALS | DATE | REV |
| DRAWN @AC | 2/1/16 | 01 |
| CHECKED | | |
| SIZE | DRAWING No. | REV |
| C | PSC-4171-01 | 01 |
| DO NOT SCALE DRAWING | | SHEET 1 OF 2 |

32-Lead VFQFN Package Outline and Package Dimensions, continued



Ordering Information

Table 8. Ordering Information

| Part/Order Number | Marking | Package | Shipping Packaging | Temperature |
|-------------------|---------------------|--------------------------|--------------------|---------------|
| 8T74S208C-01NLGI | IDT8T74S208C-01NLGI | 32-Lead VFQFN, Lead-Free | Tray | -40°C to 85°C |
| 8T74S208C-01NLGI8 | IDT8T74S208C-01NLGI | 32-Lead VFQFN, Lead-Free | Tape & Reel | -40°C to 85°C |

Datasheet Revision History

| Revision Date | Description of Change |
|-----------------|--|
| August 22, 2016 | This is the first release of the <i>8T74S208C-01 Datasheet</i> . |

Silicon Revision History

| Revision Date | Description of Change |
|---|--|
| August 22, 2016 Revision C: 8T74S208A-01NLGI to 8T74S208C-01NLGI | <ul style="list-style-type: none"> ▪ Datasheet part number updated from 8T74S208A-01 to 8T74S208C-01. ▪ Power Supply DC Characteristics Table: <ul style="list-style-type: none"> – I_{DD} typical parameter from 41mA to 54mA, maximum from 49mA to 64mA. – I_{DDO} typical parameter from 153mA to 155mA, maximum from 176mA to 182mA. ▪ AC Characteristics Table: <ul style="list-style-type: none"> – t_{PD}: <ul style="list-style-type: none"> (FSEL[1:0] = 00 row), maximum parameter from 620ps to 700ps. (FSEL[1:0] = 01 row), maximum parameter from 800ps to 880ps. (FSEL[1:0] = 10 row), maximum parameter from 920ps to 1080ps. (FSEL[1:0] = 11 row), maximum parameter from 1050ps to 1180ps. – t_R / t_F maximum parameter from 350ps to 370ps. ▪ The Power Considerations section has been updated to reflect the changes in the Power Supply DC Characteristics Table. |



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